查询2SB1231供应商 捷多邦，专业PCB打样工厂，24小时加急出货

Ordering number: EN3260A

SANYO

No.3260A

2SB1231/2SD1841

2SB1231 : PNP Epitaxial Planar Silicon Transistor
2SD1841 : NPN Triple Diffused Planar Silicon Transistor

100V/25A Switching Applications

Features

- Large current capacity and wide ASO.
- Low saturation voltage.

Applications

- Motor drivers, relay drivers, converters, and other general high-current switching applications

( ) : 2SB1231

Absolute Maximum Ratings at Ta = 25°C

				unit
Collector-to-Base Voltage	V_{CBO}		(−)110	V
Collector-to-Emitter Voltage	V_{CEO}		(−)100	V
Emitter-to-Base Voltage	V_{EBO}		(−)6	V
Collector Current	I_C		(−)25	A
Collector Current(Pulse)	I_{CP}		(−)40	A
Base Current	I_B		(−)8	A
Collector Dissipation	P_C		3.0	W
		Tc = 25°C	120	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta = 25°C

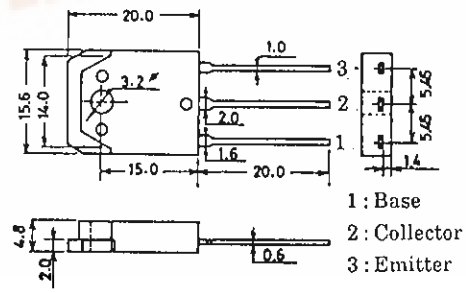
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = (−)100V, I_E = 0			(−)0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = (−)5V, I_C = 0			(−)0.1	mA
DC Current Gain	$h_{FE}(1)$	V_{CE} = (−)2V, I_C = (−)2.5A	50※		140※	
	$h_{FE}(2)$	V_{CE} = (−)2V, I_C = (−)10A	20			
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = (−)10A, I_B = (−)1A			(−)0.8	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = (−)10A, I_B = (−)1A			(−)1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C = (−)1mA, I_E = 0	(−)110			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C = (−)5mA, R_{BE} = ∞	(−)100			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E = (−)1mA, I_C = 0	(−)6			V

※ : For the $h_{FE(1)}$ of the 2SB1231/2SD1841, specify at least two ranks in principle.

50 P 100	70 Q 140

Package Dimensions 2022A

(unit : mm)



SANYO: TO3PB

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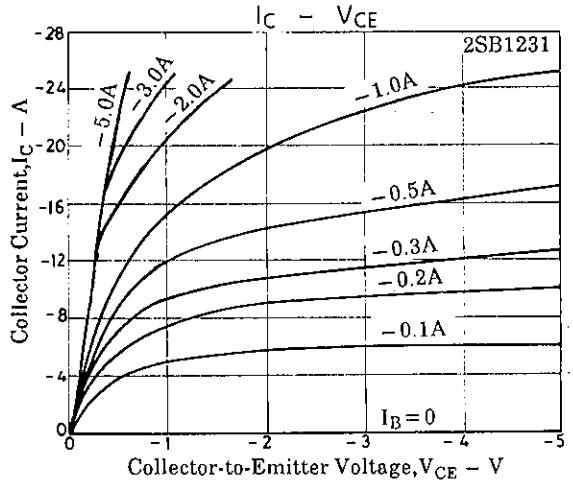
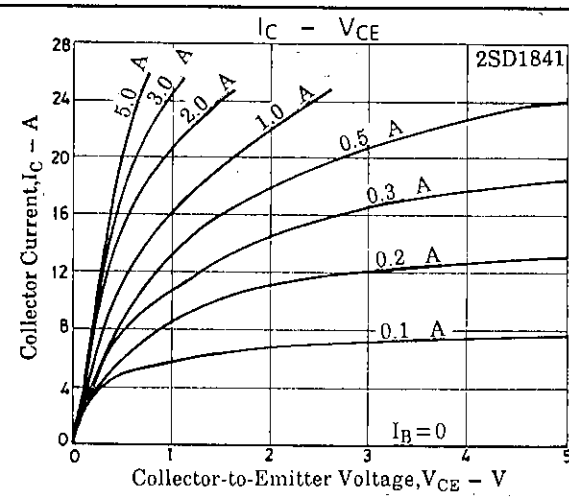
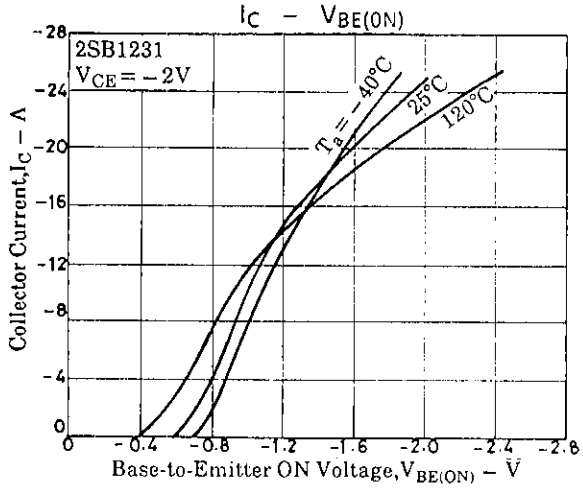
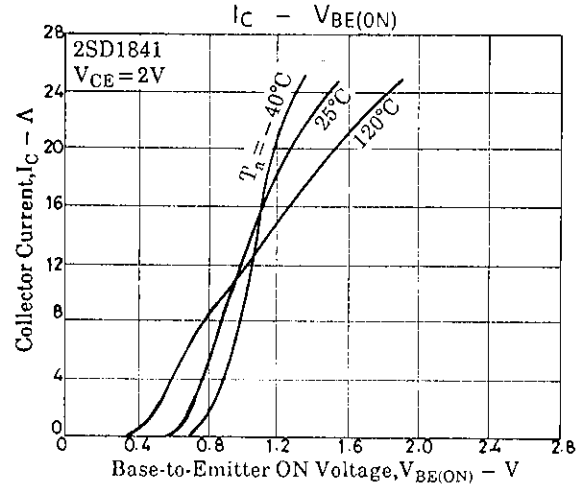
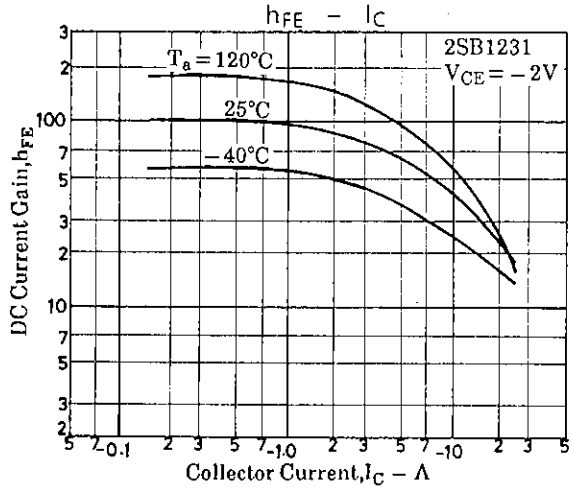
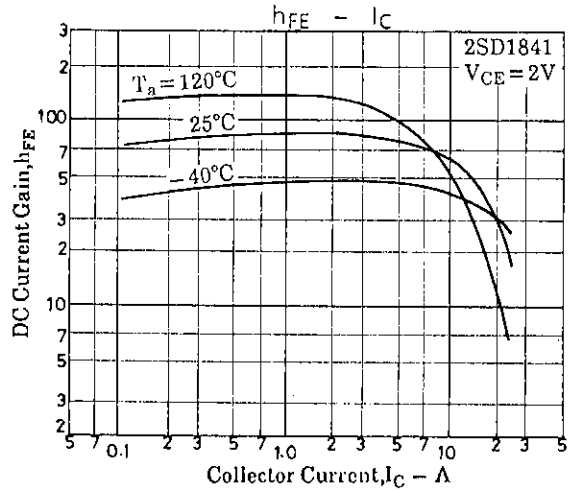

IC – VCE
2SB1231
–5.0A
–3.0A
–2.0A
–1.0A
–0.5A
–0.3A
–0.2A
–0.1A
IB = 0
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V

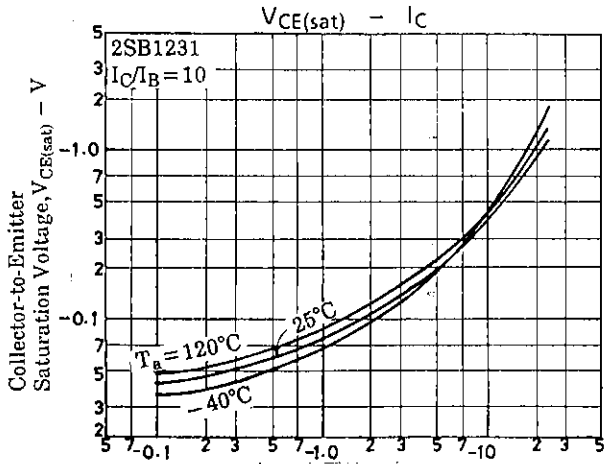

IC – VCE
2SD1841
5.0 A
3.0 A
2.0 A
1.0 A
0.5 A
0.3 A
0.2 A
0.1 A
IB = 0
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V

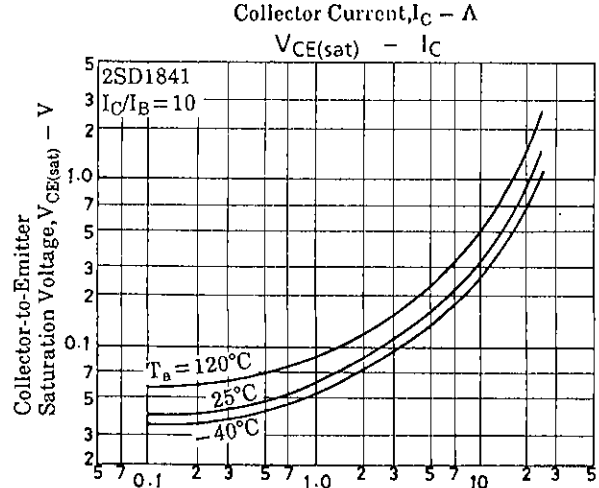

IC – VBE(ON)
2SB1231
VCE = –2V
Ta = –40°C
25°C
120°C
Collector Current, IC – A
Base-to-Emitter ON Voltage, VBE(ON) – V

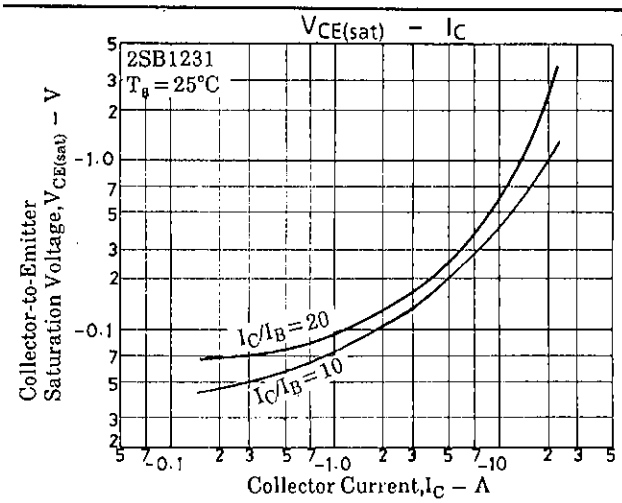

IC – VBE(ON)
2SD1841
VCE = 2V
Ta = –40°C
25°C
120°C
Collector Current, IC – A
Base-to-Emitter ON Voltage, VBE(ON) – V

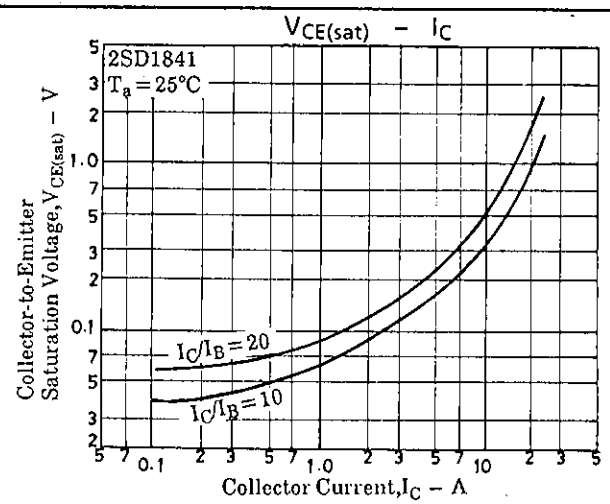

hFE – IC
2SB1231
VCE = –2V
Ta = 120°C
25°C
–40°C
DC Current Gain, hFE
Collector Current, IC – A

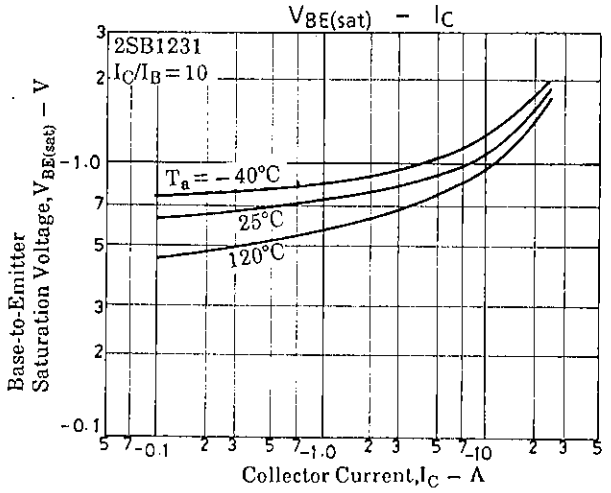

hFE – IC
2SD1841
VCE = 2V
Ta = 120°C
25°C
–40°C
DC Current Gain, hFE
Collector Current, IC – A

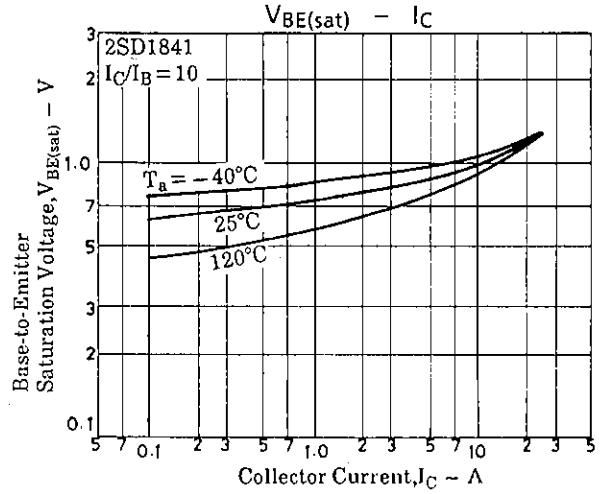

VCE(sat) – IC
2SB1231
IC/IB = 10
Ta = 120°C
25°C
–40°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V

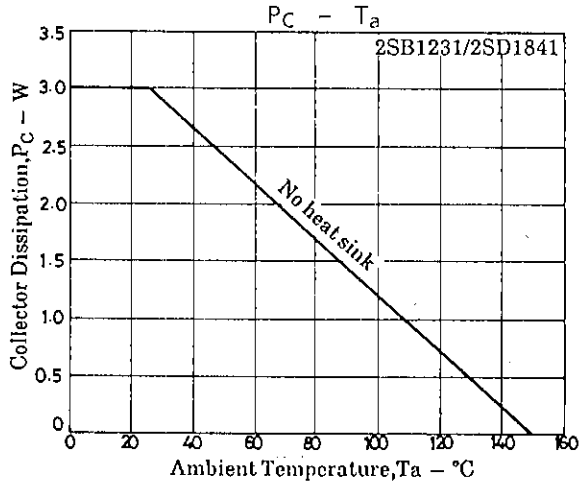

VCE(sat) – IC
2SD1841
IC/IB = 10
Ta = 120°C
25°C
–40°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V

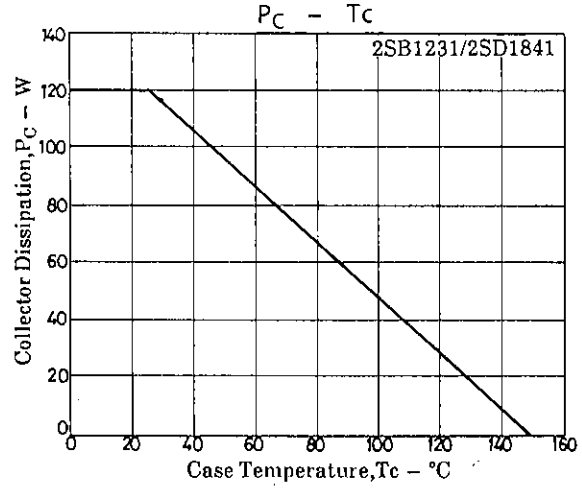

VCE(sat) – IC
2SB1231
Ta = 25°C
IC/IB = 20
IC/IB = 10
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A

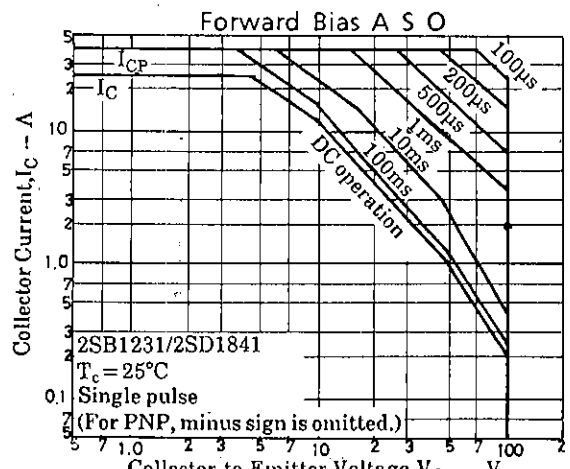

VCE(sat) – IC
2SD1841
Ta = 25°C
IC/IB = 20
IC/IB = 10
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A


VBE(sat) – IC
2SB1231
IC/IB = 10
Ta = –40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A


VBE(sat) – IC
2SD1841
IC/IB = 10
Ta = –40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A


PC – Ta
2SB1231/2SD1841
No heat sink
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C


PC – Tc
2SB1231/2SD1841
Collector Dissipation, PC – W
Case Temperature, Tc – °C


Forward Bias A S O
ICP
IC
100μs
200μs
500μs
1ms
10ms
100ms
DC operation
2SB1231/2SD1841
Tc = 25°C
Single pulse
(For PNP, minus sign is omitted.)
Collector Current, IC – A

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